

MURS140 & MURS160

Vishay General Semiconductor

Surface Mount Ultrafast Plastic Rectifier

Major Ratings and Characteristics

I _{F(AV)}	1.0 A			
V _{RRM}	400 V, 600 V			
I _{FSM}	35 A			
t _{rr}	50 ns			
V _F	1.05 V			
T _j max.	175 °C			



DO-214AA (SMB)

Epoxy meets UL 94V-0 Flammability rating

Polarity: Color band denotes cathode end

J-STD-002B and JESD22-B102D

E3 suffix for commercial grade

Terminals: Matte tin plated leads, solderable per

Mechanical Data

Case: DO-214AA (SMB)

Features

- · Glass passivated chip junction
- · Ideal for automated placement
- · Ultrafast reverse recovery time
- Low switching losses, high efficiency
- · High forward surge capability
- Meets MSL level 1, per J-STD-020C
- Solder Dip 260 °C, 40 seconds

Typical Applications

For use in high frequency rectification and freewheeling application in switching mode converters and inverters for consumer, computer and Telecommunication

Maximum Ratings

 $T_A = 25$ °C unless otherwise specified

Parameter	Symbol	MURS140	MURS160	Unit
Device Marking Codes		MG	MJ	
Maximum repetitive peak reverse voltage	V _{RRM} 400 600		V	
Working peak reverse voltage	V _{RWM}	400	600	V
Maximum DC blocking voltage	V _{DC}	400	600	V
	I _{F(AV)}	1.0 2.0		A
Peak forward surge current 8.3 ms single half sine-wave superimposed on rated load	I _{FSM}	35		A
Operating junction and storage temperature range	T _J , T _{STG}	- 65 to + 175		О°

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Electrical Characteristics

 $T_A = 25 \ ^{\circ}C$ unless otherwise specified#

Parameter	Test condition		Symbol	MURS 140	MURS 160	Unit
Maximum instantaneous forward voltage ⁽¹⁾	at I _F = 1.0 A, at I _F = 1.0 A,	T _J = 25 °C T _J = 150 °C	V _F	1.: 1.:	25 05	V
Maximum instantaneous reverse current at rated DC blocking voltage ⁽¹⁾		T _J = 25 °C T _J = 150 °C	Ι _R	5 15	.0 50	μΑ
Maximum reverse recovery time	at $I_F = 0.5 \text{ A}$, $I_R = 1.0 \text{ A}$, $I_{rr} = 0.2$	25 A	t _{rr}	5	0	ns
Maximum reverse recovery time	at I _F = 1.0 A, di/dt = 50 A/µs, V _I I _{rr} = 10 % I _{RM}	_R = 30 V,	t _{rr}	7	5	ns
Maximum forward recovery time	at $I_F = 1.0 \text{ A}$, di/dt = 100 A/µs, re	ecovery to 1.0 V	t _{fr}	5	0	ns

Notes:

(1) Pulse test: t_p = 300 μs pulse, duty cycle \leq 2 %

Thermal Characteristics

 T_A = 25 °C unless otherwise specified

Parameter	Symbol	MURS140	MURS160	Unit
Typical thermal resistance junction to ambient	$R_{ extsf{ heta}JL}$	13		C/W

Ratings and Characteristics Curves

 $(T_A = 25 \circ C \text{ unless otherwise noted})$



Figure 1. Forward Current Derating Curve



Figure 2. Maximum Non-Repetitive Peak Forward Surge Current



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Figure 3. Typical Instantaneous Forward Characteristics



Figure 4. Typical Reverse Leakage Characteristics

Package outline dimensions in inches (millimeters)



Mounting Pad Layout





Figure 5. Typical Junction Capacitance



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